

1765



TSMC-01-663

March 11, 2003

To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/005,803 12/05/01

Hsin-Ching Shih et al.

DRY-WET-DRY SOLVENT-FREE PROCESS
AFTER STOP LAYER ETCH IN DUAL
DAMASCENE PROCESS

Grp. Art Unit: 1765

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56. Copies of each document is included herewith.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner of Patents and
Trademarks, Washington, D.C. 20231, on March 13, 2003.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

830 3/13/03

TSMC-01-663

Taiwan Publication Number TW432526, discloses a method for cleaning a low dielectric constant (low K) layer, applied to a semiconductor process for removing a material layer on a surface of the low K layer.

Sincerely,

A handwritten signature in black ink, appearing to be 'SBA', written over a horizontal line.

Stephen B. Ackerman,
Reg. No. 37761